



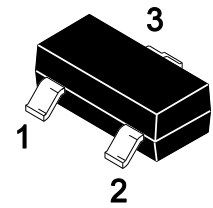
# BAV199<sup>\*</sup>

## Silicon Epitaxial Planar Switching Diode

### Features

- Glass Passivated Chip Junction
- Low Leakage Current

### Package

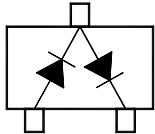


1. Anode1 2. Cathode2  
3. Cathode1、Anode2

Marking Code : AJ

### Equivalent Circuit

3. Cathode1、Anode2



1. Anode1 2. Cathode2

### Electrical Characteristics (at $T_J = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Continuous Reverse Voltage	$V_R$	70	V
Continuous Forward Current (Double Diode Load)	$I_F$	215	mA
Maximum Peak Forward Current	$I_{FM}$	500	mA
Non-Repetitive Peak Forward Surge Current at $t=8.3\text{ms}$	$I_{FSM}$	1	A
Maximum Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-50 to +150	$^\circ\text{C}$

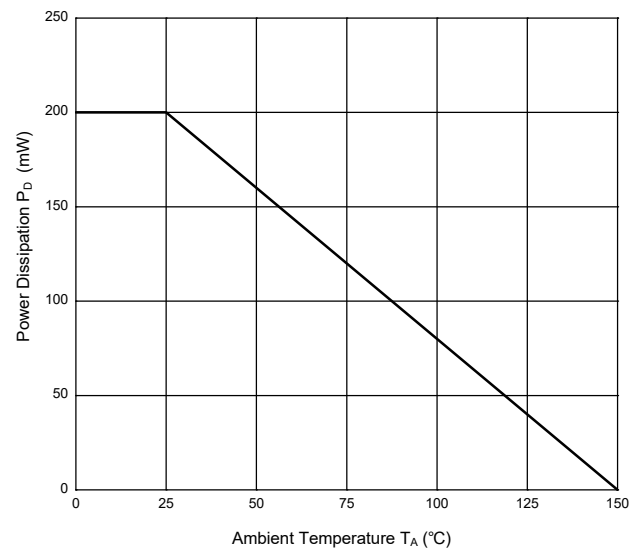
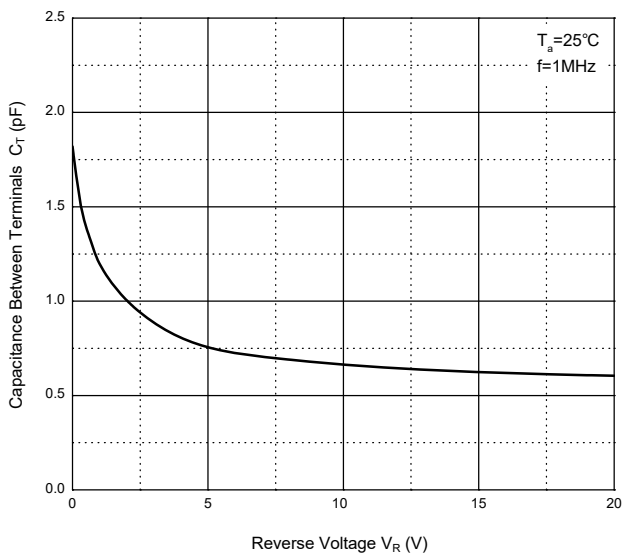
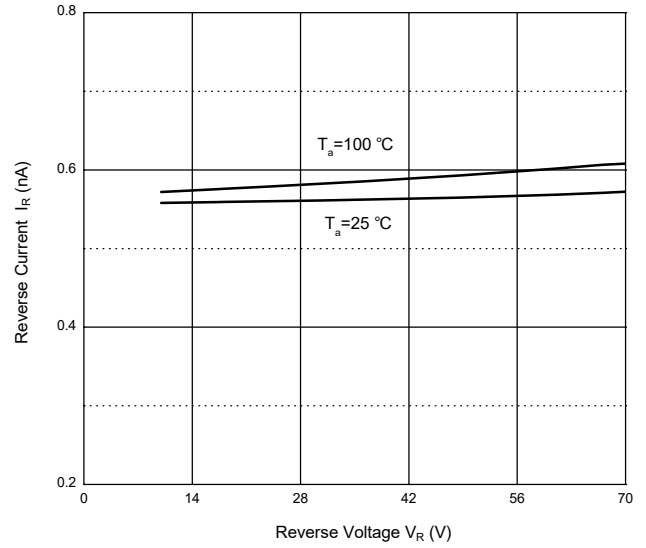
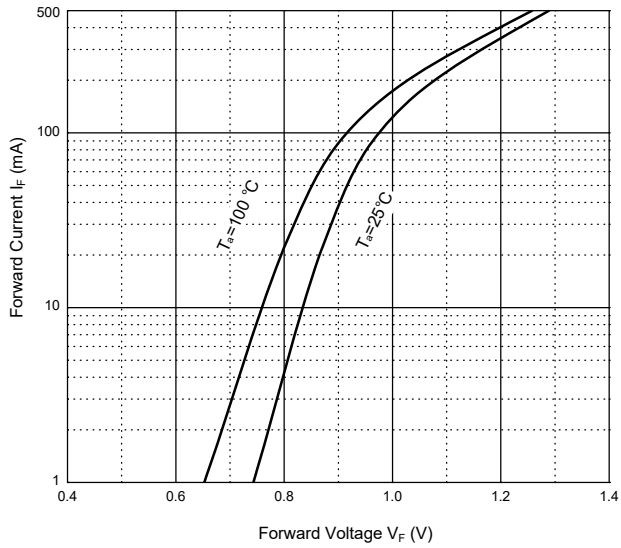
### Electrical Characteristics (at $T_J = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	$V_F$	--	0.9 1 1.1 1.25	V
Reverse Current at $V_R = 70\text{ V}$	$I_R$	--	5	nA
Typical Junction Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_j$	--	2	pF
Maximum Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ , $I_{rr} = 0.1 \times I_R$ , $R_L = 100\Omega$	$T_{rr}$	--	3	$\mu\text{s}$



# BAV199 Silicon Epitaxial Planar Switching Diode

## Typical Characteristic Curves





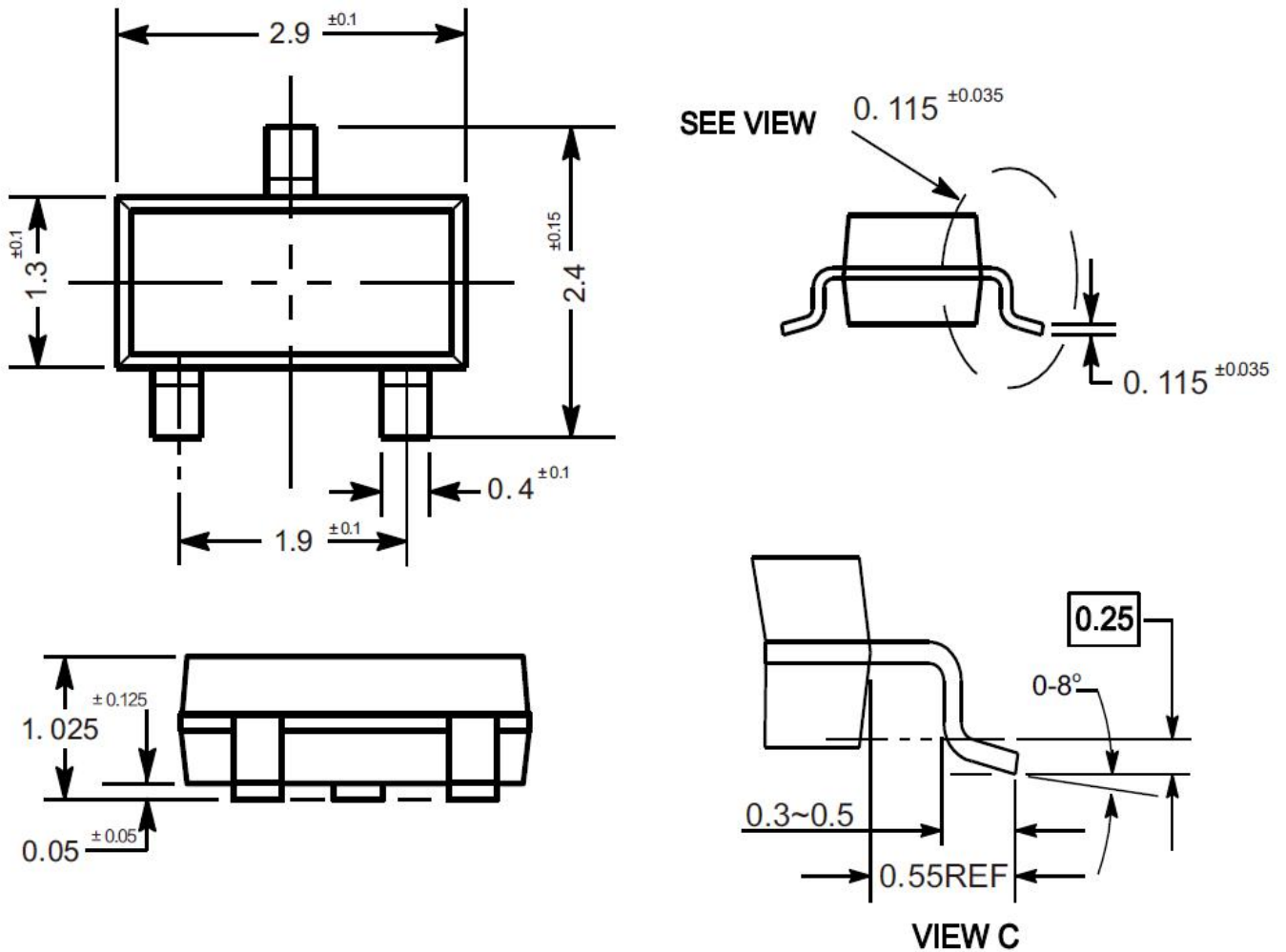
# BAV199

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23

Dimensions in mm



### Ordering Information

Device	Package	Shipping
BAV199	SOT-23	3,000PCS/Reel&7inches